

ON THE ORIGIN OF THE HEAVY-FERMION-LIKE
BEHAVIOR OF THE HEUSLER-TYPE
 $\text{Fe}_{3-x}\text{V}_x\text{M}$ (M=Al,Ga) ALLOYS*

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The electronic structure of $\text{Fe}_{3-x}\text{V}_x\text{M}$ (M=Al, Ga) alloys was investigated by *ab initio* method. Magnetic and non-magnetic band structure of $\text{Fe}_{3-x}\text{V}_x\text{M}$ was calculated for concentrations $x = 0.0-1.0$. Calculations have shown that the transition from magnetic to non-magnetic state is accompanied by the qualitative changes in the band structure in the vicinity of the Fermi level (ε_F). For concentrations $0.5 \leq x \leq 1$ the Density Of States (DOS) at ε_F in both magnetic states display a sharp peak composed solely of the $3d$ states of impurity Fe-AS atom (Fe atom at nominally V atom position of Fe_2VAl Heusler compound). In the magnetic state only majority-spin states enter the DOS near ε_F . The quasi-gap around the ε_F found in Fe_2VM is filled up by $3d\uparrow$ states of Fe-AS which produce the sharp structures at ε_F . Transition to the non-magnetic state results in the narrowing and strengthening of the peak of Fe-AS $3d$ -states DOS at ε_F and the opening of the well-defined gap just above the Fermi level. The changes of the DOS around ε_F connected with the variation of Fe-AS concentration and magnetic transition explain the peculiar behavior of the electrical resistivity observed experimentally.

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Recently the pseudo-binary $\text{Fe}_{3-x}\text{V}_x\text{M}$ (M=Al, Ga) alloys with DO_3 crystal structure are the subject of the intensive experimental [1-5] and theoretical [6-8] investigations. The alloys attract the attention of many authors because they exhibit a variety of properties unique among the $3d$ -intermetallic alloys. At composition $x = 1$ the Heusler Fe_2VM compounds

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behave in a manner typical for insulators. In the entire measured temperatures (*e.g.* from 2K to above 1200 K in case of Fe_2VAl [4]) the resistivity of Fe_2VM decreases with increasing temperature. The resistivity of the end ($x = 0$) compounds (Fe_3Al and Fe_3Ga) show a metallic behavior. When in these compounds the Fe atoms are replaced by V atoms, the character of the temperature dependence of the electrical resistivity changes when the sample undergoes the transition from magnetic to para- or non-magnetic state. At low temperatures the resistivity increases with temperature and forms a maximum near Curie temperature T_C . Above T_C it decreases with increasing temperature. With increasing V composition the temperature region with negative resistivity slope expands in parallel with reduction in T_C . On the other hand, the Fe_2VAl compound is characterized by anomalously large value of the electronic specific-heat coefficient γ [2,4] and by the presence of the Fermi edge in the XPS spectrum [2]. This behavior can suggest that Fe_2VAl is a possible candidate for a 3d heavy-fermion system [2,4].

Though the electronic structure of Fe_2VM was the subject of *ab initio* band structure calculations, there are no results describing the role of the Fe-AS defect atoms in nearly stoichiometric Heusler compositions. The aim of the presented band structure calculations was to extend the super-cell calculations reported in [7] to cover the wider vanadium concentration range in $\text{Fe}_{3-x}\text{V}_x\text{Al}$. The $\text{Fe}_{3-x}\text{V}_x\text{Ga}$ alloys were calculated in order to clarify the role of M atoms in the alloys. The calculations were performed with the use of the *tight-binding linear muffin-tin orbital* (TB-LMTO) method [9]. To simulate the disorder in $\text{Fe}_{3-x}\text{V}_x\text{M}$ alloys the super-cell methodology of alloy modeling was used. The details of input data preparation and approximation used were shortly discussed in our previous paper [10].

The most important magnetic results for $\text{Fe}_{3-x}\text{V}_x\text{Al}$ we already presented and shortly discussed in [10]. The calculated magnetic structure of $\text{Fe}_{3-x}\text{V}_x\text{Ga}$ was found very similar. The calculations for $x = 0.5\text{--}0.94$ confirmed the conclusions drawn from experiments [3] about the existence of magnetic clusters. For small concentrations of Fe-AS atoms calculations have shown that the Fe-AS impurities together with eight surrounding Fe atoms form the magnetic clusters. The magnetic moment of Fe-AS atoms is large ($\sim 2.7 \mu_B$) and robust against the V concentration in the range of $x = 0.5\text{--}0.9375$. The eight iron atoms surrounding the Fe-AS one are only slightly polarized and for concentration range $x = 0.75\text{--}0.9375$ their magnetic moments do not exceed $0.2 \mu_B$. Within this concentration range the effective, cluster magnetic moment is of order of $4 \mu_B$ and does not depend on x . Due to the large spatial separation of these clusters their direct magnetic exchange interaction can be neglected. Existence of such magnetic defects in Fe_2VM compounds is responsible for the marginally magnetic character of these compounds observed experimentally. Furthermore, the

scattering of electrons on such non-interacting magnetic defects may result in negative magneto-resistance also observed in the $\text{Fe}_{3-x}\text{V}_x\text{M}$ alloys at temperatures below Curie temperature T_C [11, 12]. Estimations based on the calculated total energy difference between the magnetic and non-magnetic solutions for $\text{Fe}_{3-x}\text{V}_x\text{M}$ ($x = 0.75\text{--}0.9375$) results in T_C of roughly the same values as the measured ones. This coincidence indicate that for $x \simeq 1.0$ the magnetic transition leads to the disappearance of local magnetic moments and consequently to the non-magnetic state of $\text{Fe}_{3-x}\text{V}_x\text{M}$ alloys above T_C .

The most interesting result of the calculations performed for the $\text{Fe}_{3-x}\text{V}_x\text{M}$ alloys with $x = 0.5\text{--}0.9375$ is the behavior of the DOS around the Fermi level (ε_F). In the Heusler Fe_2VM compounds the total DOS (Fig. 1) in the vicinity of ε_F is characterized by a deep valley (quasi-gap) with the very small values of DOS at ε_F and width of ~ 0.5 eV. Similar results were already reported by other authors [6, 7].

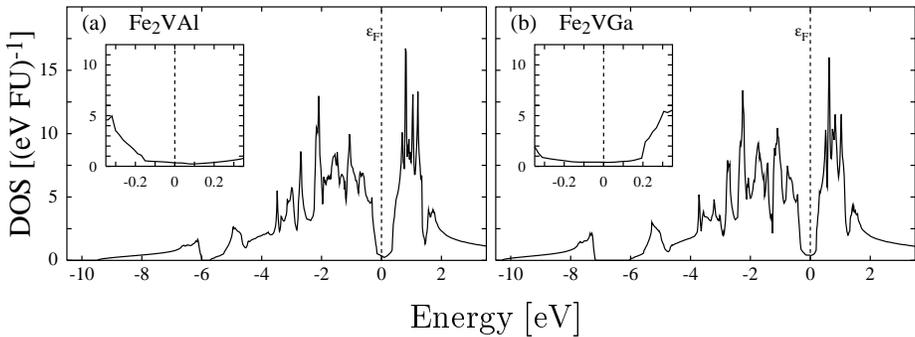


Fig. 1. Total density of states (DOS) of Fe_2VM ($\text{M}=\text{Al}$ and Ga) compounds. Vertical dash lines mark the Fermi energy (ε_F). Inserts show the DOS in the vicinity of ε_F .

The picture changes qualitatively in the presence of Fe-AS impurities (Fig. 2). Parts (a)–(d) and (a₁)–(d₁) of Fig. 2 show the total DOS of $\text{Fe}_{3-x}\text{V}_x\text{Al}$ and $\text{Fe}_{3-x}\text{V}_x\text{Ga}$ calculated in magnetic and non-magnetic state of the alloys. The magnetic Fe-AS defect atoms replacing the V atoms in both Fe_2VM compounds diminish slightly the width of the quasi-gap and lead to the appearance of the peak of the majority d -states DOS located exactly at ε_F . From the rest of the valence band it is separated by two dips of low DOS. In $\text{Fe}_{2.06}\text{V}_{0.94}\text{Al}$ the Fermi level lies at the lower boundary of the peak and a dip below changes to a narrow gap of width of $\simeq 0.05$ eV. In principle the hopping is possible only within the narrow band which originate from $3d\uparrow$ states of Fe-AS atoms. With decreasing x the carrier concentration available near the ε_F grows so the residual resistivity should decrease. This effect was observed in both $\text{Fe}_{3-x}\text{V}_x\text{M}$ alloys [1, 2, 4].

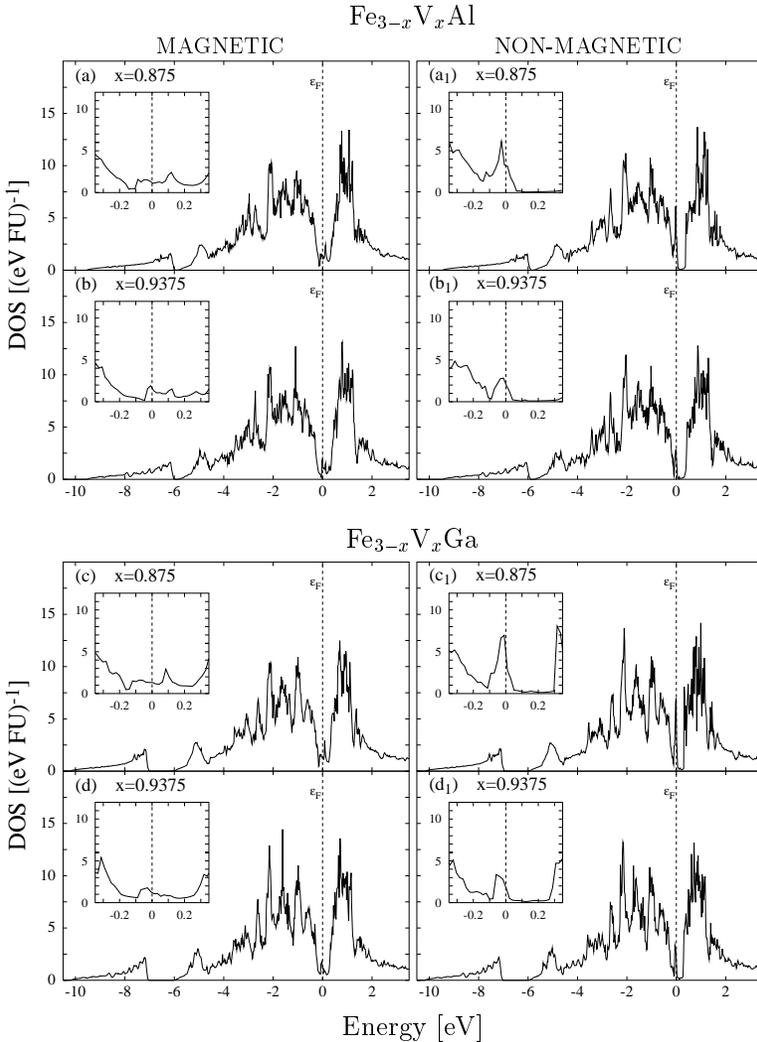


Fig. 2. Total DOS of the $\text{Fe}_{3-x}\text{V}_x\text{M}$ with $\text{M}=\text{Al}$ (parts (a), (b)) and $\text{M}=\text{Ga}$ (parts (c), (d)) for $x = 0.875$ and 0.9375 in magnetic ((a),(b),(c),(d)) and non-magnetic ((a₁),(b₁),(c₁),(d₁)) states. (For other notations see Fig. 1.)

The transition to the non-magnetic state leads again to the qualitative changes in DOS near ε_{F} . The $3d$ -peak at ε_{F} grows, becomes sharper and shifts to higher binding energies. The ε_{F} shifts to upper boundary of the peak and the energy gap of 0.2 – 0.3 eV width opens above the ε_{F} . All these peculiarities of DOS near ε_{F} originate from the d -states of Fe-AS atoms hybridized with the d -states of surrounding Fe atoms in the octahedral co-

ordination. The hybridization with other electronic states located around the ε_F is hardly visible.

The existence of the energy gap at ε_F in nonmagnetic $\text{Fe}_{3-x}\text{V}_x\text{M}$ explains the observed negative resistivity slope for $T > T_C$. On the other hand the presence of the narrow and relatively high peak of DOS at ε_F provides an explanation for the observed high values of the electronic specific-heat coefficient. In summary it can be concluded that the unusual (typical for $4f$ heavy-fermion compounds) electronic, magnetic and transport properties of Fe_2VM compounds can be explained by the presence of Fe-AS defects whose role is analogous to that of $4f$ -elements in heavy-fermion compounds.

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